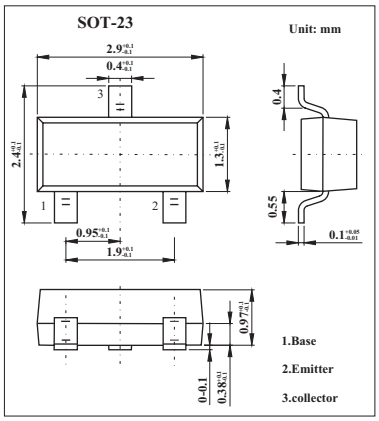
PNP Silicon AF Transistors
KC807A(BC807A)



■ Features

- For general AF applications.
- High collector current.
- High current gain.
- Low collector-emitter saturation voltage.

■ Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	-50	V
Collector-emitter voltage	V_{CEO}	-45	V
Emitter-base voltage	V_{EBO}	-5	V
Collector current (DC)	I_C	-500	mA
Peak collector current	I_{CM}	-1	A
Base current	I_B	-100	mA
power dissipation	P_D	310	mW
Junction temperature	T_j	150	℃
Storage temperature	T_{stg}	-65 to +150	℃

■ Electrical Characteristics Ta = 25℃

Parameter		Symbol	Testconditons	Min	Typ	Max	Unit
Collector-to-base breakdown voltage		V_{CBO}	I_C = -10 μA, I_E = 0	-50			V
Collector-to-emitter breakdown voltage		V_{CEO}	I_C = -10 mA, I_B = 0	-45			V
Emitter-to-base breakdown voltage		V_{EBO}	I_E = -10 μA, I_C = 0	-5			V
Collector cutoff current		I_{CBO}	V_{CB} = -25 V, I_E = 0			-100	nA
			V_{CB} = -25 V, I_E = 0 , T_A = 150℃			-50	μA
Emitter cutoff current		I_{EBO}	V_{EB} = -4 V, I_C = 0			-100	nA
DC current gain *	KC807A-16	h_{FE}	I_C = -100 mA, V_{CE} = -1 V	100	160	250	
	KC807A-25			160	250	400	
	KC807A-40			250	350	630	
Collector saturation voltage *		$V_{CE(sat)}$	I_C = -500 mA, I_B = -50 mA			-0.7	V
Base to emitter voltage *		$V_{BE(sat)}$	I_C = -500 mA, I_B = -50 mA			-1.2	V
Collector-base capacitance		C_{Cb}	V_{CB} = -10 V, f = 1 MHz		10		pF
Emitter-base capacitance		Ceb	V_{EB} = -0.5 V, f = 1 MHz		60		pF
Transition frequency		f_T	I_C = -50 mA, V_{CE} = -5 V, f = 100 MHz		200		MHz

* Pulsed: PW ≤ 350 μs, duty cycle ≤ 2%

■ Marking

NO.	KC807A-16	KC807A-25	KC807A-40
Marking	5A	5B	5C